AUTOMOTIVE

COMPLIANT HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt®



Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
$I_{F(AV)}$	3 A			
V _R	100 V			
V _F at I _F	0.74 V			
t _{rr}	30 ns			
T _J max.	175 °C			
Package	SlimSMA (DO-221AC)			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- · Specific for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SlimSMA (DO-221AC)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		100	V	
Average rectified forward current	I _{F(AV)}	T _C = 145 °C ⁽¹⁾	3	۸	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	85	_ A	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	100	-	-	
Forward voltage	V _F	I _F = 3 A	-	0.86	0.93	V
		I _F = 3 A, T _J = 125 °C	-	0.74	0.78	
Reverse leakage current	I _R	V _R = V _R rated	-	-	2	uА
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	0.5	8	μΑ
Junction capacitance	C _T	V _R = 100 V	-	13	-	pF



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	26	-	
Reverse recovery time t _{rr}		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	30	ns
	T _J = 25 °C		-	18	-		
		T _J = 125 °C		-	26	-	
Peak recovery current I _{RRM}		T _J = 25 °C	$I_F = 3 \text{ A}$ $dI_F/dt = 200 \text{ A/µs}$ $V_R = 160 \text{ V}$	-	2.5	-	Α
	IRRM	T _J = 125 °C		-	4	-	A
Reverse recovery charge	0	T _J = 25 °C		-	23	-	nC
	Q_{rr}	T _J = 125 °C		-	50	-	IIC

THERMAL - MECHANICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	8	10	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	91	110	C/VV
Annyayimata Waight				0.032		g
Approximate Weight			0.0011 o		OZ.	
Marking device		Case style SlimSMA (DO-221AC)		31	H1	

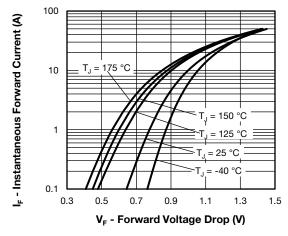


Fig. 1 - Typical Forward Voltage Drop Characteristics

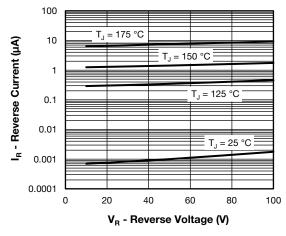


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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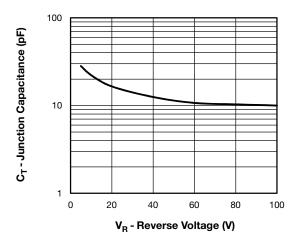


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

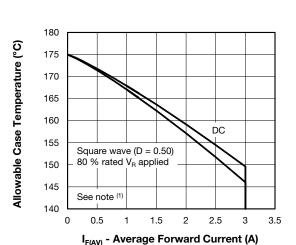


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

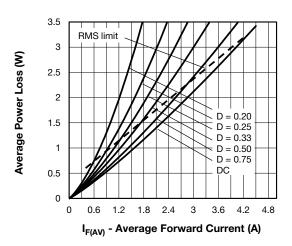


Fig. 5 - Forward Power Loss Characteristics

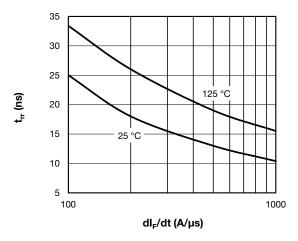


Fig. 6 - Typical Reverse Recovery vs. dl_F/dt

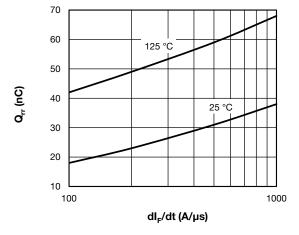


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see Fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$

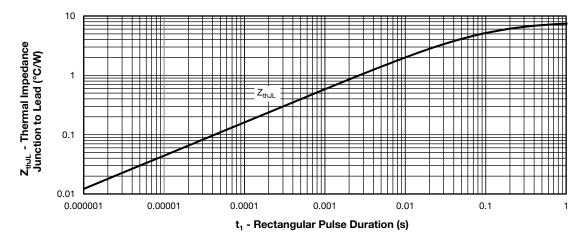


Fig. 8 - Typical Thermal Impedance ZthJL Junction-to-Lead

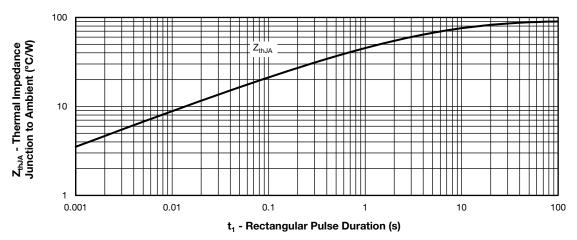
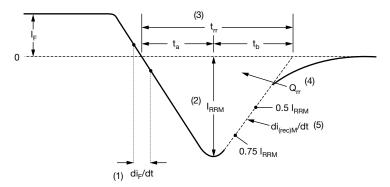


Fig. 9 - Typical Thermal Impedance Z_{thJA} Junction-to-Ambient



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

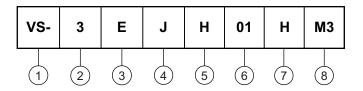
Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (3 = 3 A)

Circuit configuration:

E = single diode

J = SlimSMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (01 = 100 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-3EJH01HM3/6A	3500	3500	7"diameter plastic tape and reel		
VS-3EJH01HM3/6B	14 000	14 000	13"diameter plastic tape and reel		

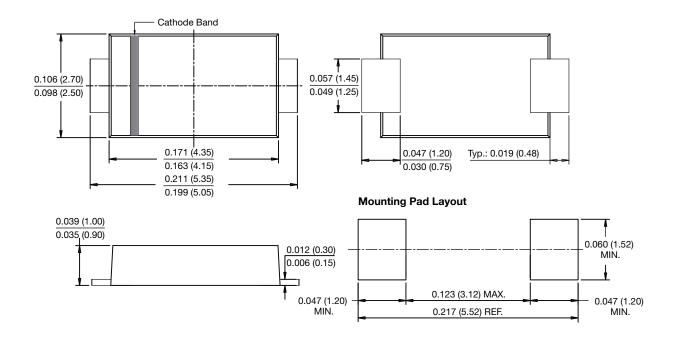
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95571			
Part marking information	www.vishay.com/doc?95562			
Packaging information	www.vishay.com/doc?88869			



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DO-221AC (SlimSMA)

DIMENSIONS in inches (millimeters)





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